PNP 5 GHz wideband transistor BFT92

DESCRIPTION

PNP transistor in a plastic SOT23 envelope.

It is primarily intended for use in RF wideband amplifiers, such as in aerial amplifiers, radar systems, oscilloscopes, spectrum analyzers, etc. The transistor features low intermodulation distortion and high power gain; due to its very high transition frequency, it also has excellent wideband properties and low noise up to high frequencies.

NPN complements are BFR92 and BFR92A.

PINNING

PIN	DESCRIPTION
Code: W1p	
1	base
2	emitter
3	collector

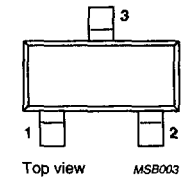


Fig.1 SOT23.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–20	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
I_C	DC collector current		–	–25	mA
P_{tot}	total power dissipation	up to T_s = 95 °C; note 1	–	300	mW
f_T	transition frequency	I_C = –14 mA; V_{CE} = –10 V; f = 500 MHz	5	–	GHz
C_{re}	feedback capacitance	I_C = –2 mA; V_{CE} = –10 V; f = 1 MHz	0.7	–	pF
G_{UM}	maximum unilateral power gain	I_C = –14 mA; V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C	18	–	dB
F	noise figure	I_C = –5 mA; V_{CE} = –10 V; f = 500 MHz; T_{amb} = 25 °C	2.5	–	dB
d_{im}	intermodulation distortion	I_C = –14 mA; V_{CE} = –10 V; R_L = 75 Ω; V_o = 150 mV; T_{amb} = 25 °C; $f_{(p+q-r)}$ = 493.25 MHz	–60	–	dB

Note

1. T_s is the temperature at the soldering point of the collector tab.

LIMITING VALUES

In accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–20	V
V_{CEO}	collector-emitter voltage	open base	–	–15	V
V_{EBO}	emitter-base voltage	open collector	–	–2	V
I_C	DC collector current		–	–25	mA
I_{CM}	peak collector current	f > 1 MHz	–	–35	mA
P_{tot}	total power dissipation	up to T_s = 95 °C; note 1	–	300	mW
T_{stg}	storage temperature		–65	150	°C
T_j	junction temperature		–	175	°C

THERMAL RESISTANCE

SYMBOL	PARAMETER	CONDITIONS	THERMAL RESISTANCE
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	up to T_s = 95 °C; note 1	260 K/W

Note

1. T_s is the temperature at the soldering point of the collector tab.

CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

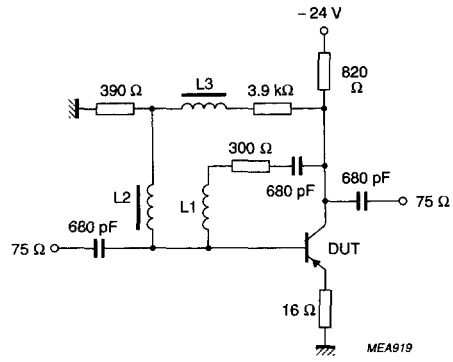
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector cut-off current	I_E = 0; V_{CB} = −10 V;	–	–	−50	nA
h_{FE}	DC current gain	I_C = −14 mA; V_{CE} = −10 V	20	50	–	
f_T	transition frequency	I_C = −14 mA; V_{CE} = −10 V; f = 500 MHz	–	5	–	GHz
C_c	collector capacitance	$I_E = i_e$ = 0; V_{CB} = −10 V; f = 1 MHz	–	0.75	–	pF
C_e	emitter capacitance	$I_C = i_c$ = 0; V_{EB} = −0.5 V; f = 1 MHz	–	0.8	–	pF
C_{re}	feedback capacitance	I_C = −2 mA; V_{CE} = −10 V; f = 1 MHz	–	0.7	–	pF
G_{UM}	maximum unilateral power gain (note 1)	I_C = −14 mA; V_{CE} = −10 V; f = 500 MHz; T_{amb} = 25 °C	–	18	–	dB
F	noise figure	I_C = −5 mA; V_{CE} = −10 V; f = 500 MHz; T_{amb} = 25 °C	–	2.5	–	dB
V_o	output voltage	note 2	–	150	–	mV

Notes

1. G_{UM} is the maximum unilateral power gain, assuming S_{12} is zero and

$$G_{UM} = 10 \log \frac{|S_{21}|^2}{(1-|S_{11}|^2)(1-|S_{22}|^2)} \text{dB}.$$

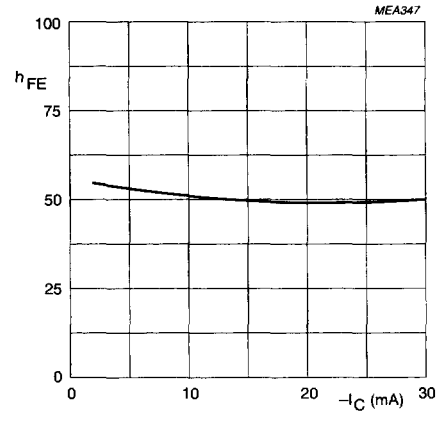
2. d_{im} = −60 dB (DIN 45004B); I_C = −14 mA; V_{CE} = −10 V; R_L = 75 Ω;
   $V_p = V_o$ at d_{im} = −60 dB; f_p = 495.25 MHz;
   $V_q = V_o$ −6 dB; f_q = 503.25 MHz;
   $V_r = V_o$ −6 dB; f_r = 505.25 MHz;
   measured at $f_{(p+q-r)}$ = 493.25 MHz.



L2 = L3 = 5 μH Ferroxcube choke, catalogue number 3122 108 20150.

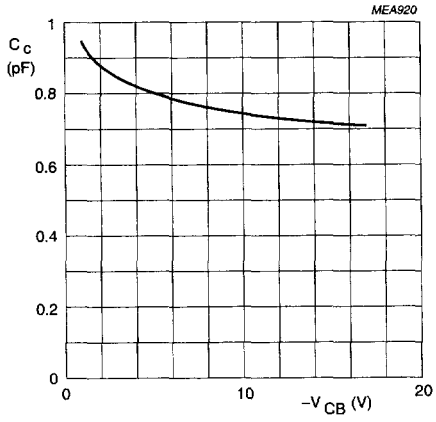
L1 = 4 turns 0.35 mm copper wire; winding pitch 1 mm; internal diameter 4 mm.

Fig.2 Intermodulation distortion test circuit.



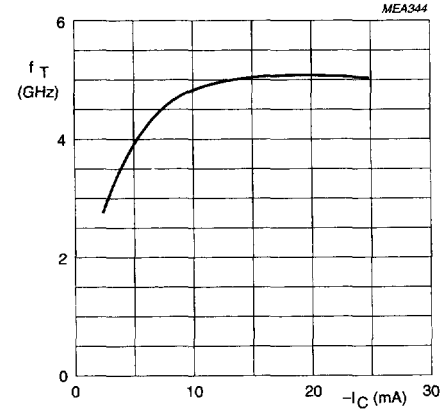
V_{CE} = −10 V; T_j = 25 °C.

Fig.3 DC current gain as a function of collector current.



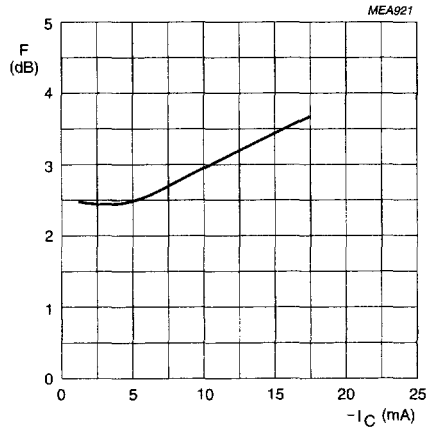
$I_E = i_e = 0$; f = 1 MHz; T_j = 25 °C.

Fig.4 Collector capacitance as a function of collector-base voltage.



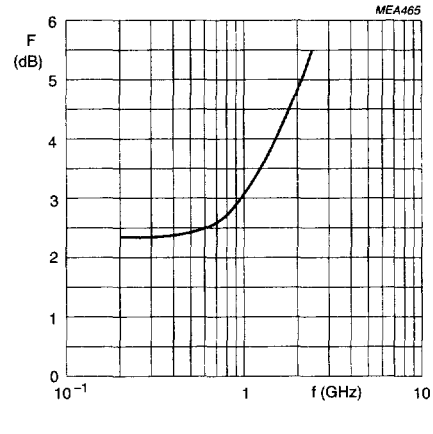
V_{CE} = −10 V; f = 500 MHz; T_j = 25 °C.

Fig.5 Transition frequency as a function of collector current.



V_{CE} = −10 V; Z_s = opt.; f = 500 MHz; T_{amb} = 25 °C.

Fig.6 Minimum noise figure as a function of collector current.



I_C = −2 mA; V_{CE} = −10 V; Z_s = opt.; T_{amb} = 25 °C.

Fig.7 Minimum noise figure as a function of frequency.